

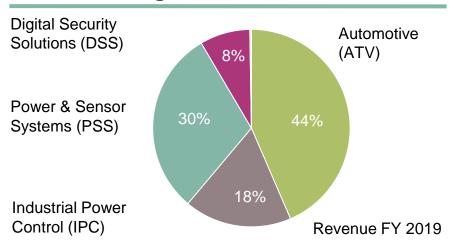
Benjamin Bernard 09.06.2020





Infineon at a glance

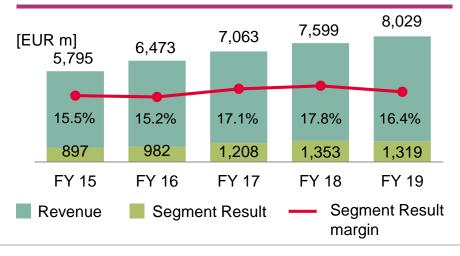
Business Segments



Employees



Financials

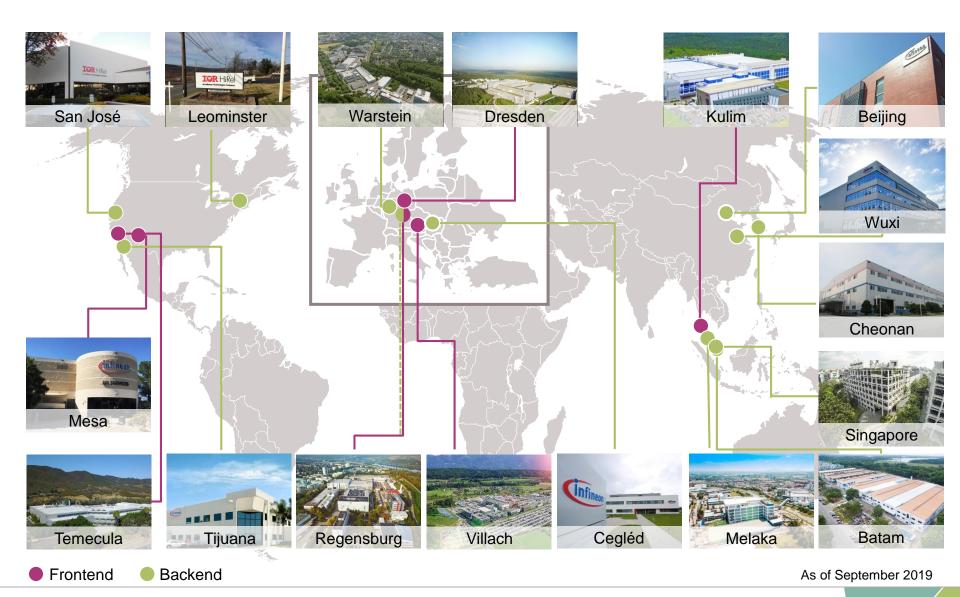


Market Position



Worldwide manufacturing sites frontend and backend



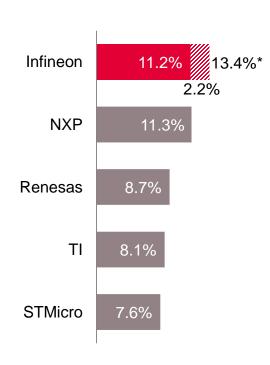




Infineon is a top player in all target markets

Automotive semiconductors

total market in 2019: \$37.2bn

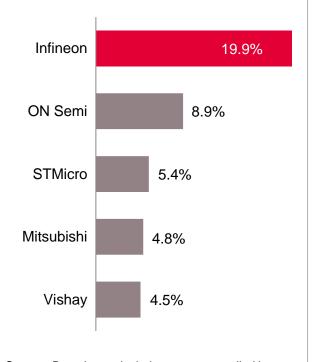


Source: Strategy Analytics, "Automotive Semiconductor Vendor Share", April 2020

*Cypress share 2.2%

Power discretes and modules

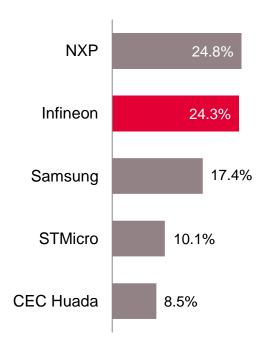
total market in 2018: \$21.0bn



Source: Based on or includes content supplied by Informa Tech (former IHS Markit Technology), "Power Semiconductor Market Share Database – 2018", September 2019

Security ICs

total market in 2018: \$3.2bn



Source: ABI Research, "Smart card & secure ICs", September 2019



Billions to be invested in the Villach site



New fully automated chip factory

Start of construction: First half of 2019

Start of production: End of 2021 Total building area: ~ 60,000 m²

Headcount: ~ 400 highly qualified jobs

Volume of investment: ~ € 1.6 billion

New R&D-building

Start of construction: Autumn of 2018

Implementation: Spring of 2020

Total building area: ~ 20,000 m²

Building capacity: 600 R&D-workplaces, of which

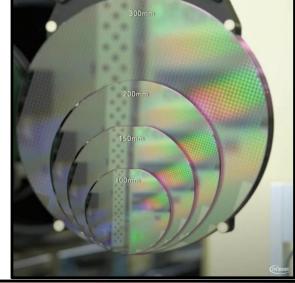
350 additional R&D-workplaces

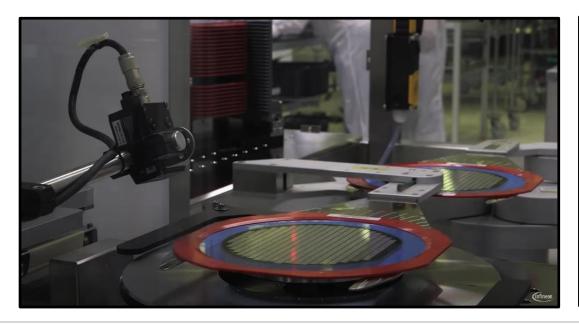
Volume of investment: € 50 million



Example: Wafer separation

- Materials: Silicon, SiC, GaN
- Thin & Ultra Thin wafers ($<100\mu m$; $<<100\mu m$)
- Wafer Size: 6", 8" and 12"
- Highest quality









Example: Ultra Thin wafer Separation

- Different thicknesses and multiple stack layers (Oxide, Metals, passivation layers) requiers fine tuning of separation process
 - => High flexibility of Laser processing due to beamshaping and splitting
- Highest reliability of separation process requierd to garantee stable and continous process results in 24/7 production

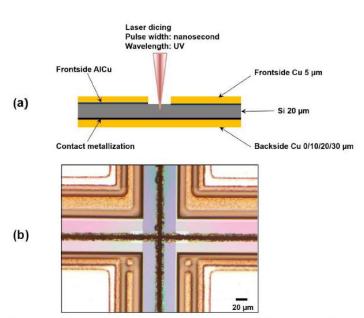


Fig. 3. (a) Laser dicing layers in the ultrathin wafer. (b) Top view of laser dicing kerf.

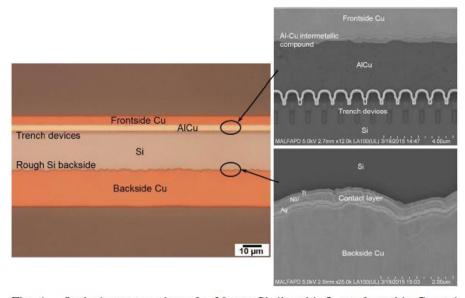


Fig. 4. Optical cross section of a 20 μ m Si die with 5 μ m frontside Cu and 20 μ m backside Cu, with SEM close-up images of the AlCu and backside contact layers.

Effect of Nanosecond Laser Dicing on the Mechanical Strength and Fracture Mechanism of Ultrathin Si Dies With Cu Stabilization Layer Michael Raj Marks, Zainuriah Hassan, *Member, IEEE*, and Kuan Yew Cheong, *Member, IEEE*

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